

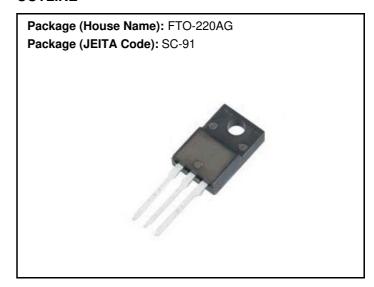
# **P40F10SN**

## Power MOSFETs 100V, 40A, N-channel

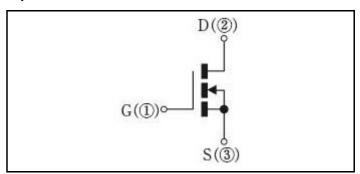
#### **Feature**

- N-channel
- Isolated Package
- · Low Ron
- 10V Gate Drive
- · Low Capacitance
- · Pb free terminal
- RoHS:Yes

### **OUTLINE**



## **Equivalent circuit**



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

| Item                           | Symbol          | Conditions                   | Ratings    | Unit |
|--------------------------------|-----------------|------------------------------|------------|------|
| Storage temperrature           | Tstg            |                              | -55 to 150 | °C   |
| Channel tempertature           | Tch             |                              | 150        | °C   |
| Drain-source voltage           | $V_{DSS}$       |                              | 100        | V    |
| Gate-source voltage            | $V_{GSS}$       |                              | ±20        | V    |
| Continuous drain current(DC)   | I <sub>D</sub>  |                              | 40         | Α    |
| Continuous drain current(Peak) | I <sub>DP</sub> | Pulse width 10μs, duty=1/100 | 160        | Α    |
| Total power dissipation        | P <sub>T</sub>  |                              | 44         | W    |
| Single avalanche current       | I <sub>AS</sub> | Starting Tch=25°C Tch≦150°C  | 37         | Α    |
| Single avalanche energy        | E <sub>AS</sub> | Starting Tch=25°C Tch≦150°C  | 68         | mJ   |
| Dielectric strenght            | Vdis            | Terminals to case, AC1min    | 2          | kV   |
| Mounting torque                | TOR             | (Recommended torque: 0.3N·m) | 0.5        | N∙m  |

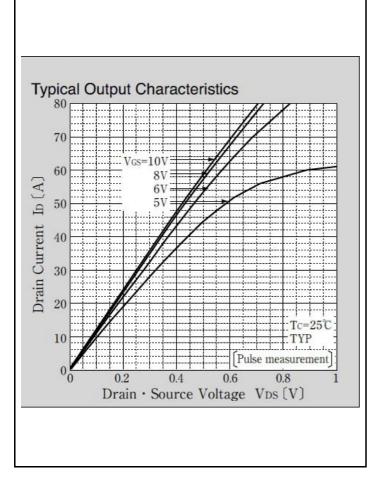
<sup>\* :</sup> See the original Specifications

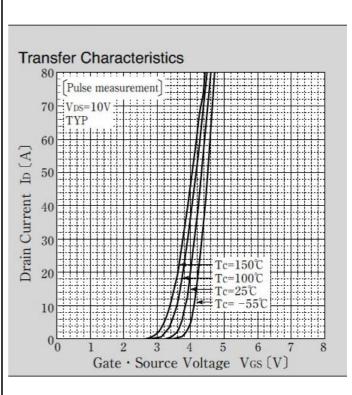
## **Electrical Characteristics** (unless otherwise specified : Tc=25°C)

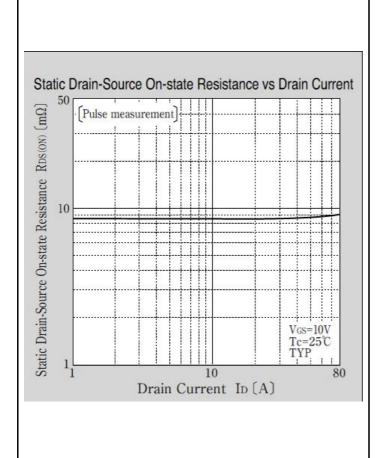
| Item                                    | Symbol              | Conditions   | Ratings |        |        | Unit |
|---|---------------------|--|---------|--------|--------|------|
|   |                     |  | MIN     | TYP    | MAX    | Unit |
| Drain-Source breakdown voltage          | $V_{(BR)DSS}$       | ID=1mA, VGS=0V   | 100     |        |        | ٧    |
| Zero gate voltage drain current         | I <sub>DSS</sub>    | VDS=100V, VGS=0V   |         |        | 1      | μA   |
| Gate-source leakage current             | I <sub>GSS</sub>    | VGS=±20V, VDS=0V   |         |        | ±0.1   | μA   |
| Forward transconductance                | 9fs                 | ID=20A, VDS=10V  | 14      |        |        | S    |
| Static drain-source on-state resistance | R <sub>DS(ON)</sub> | ID=20A, VGS=10V  |         | 0.0085 | 0.0107 | Ω    |
| Gate threshold voltage                  | Vth                 | ID=1mA, VDS=10V  | 2       | 3      | 4      | V    |
| Source-drain diode forward voltage      | $V_{SD}$            | IS=40A, VGS=0V   |         |        | 1.5    | ٧    |
| Thermal resistance                      | Rth(j-c)            | Junction to case   |         |        | 2.84   | °C/W |
| Total gate charge                       | Qg                  | VDD=80V, VGS=10V, ID=40A   |         | 92     |        | nC   |
| Gate to source charge                   | Qgs                 | VDD=80V, VGS=10V, ID=40A   |         | 23     |        | nC   |
| Gate to drain charge                    | Qgd                 | VDD=80V, VGS=10V, ID=40A   |         | 31     |        | nC   |
| Input capacitance                       | Ciss                | VDS=25V, VGS=0V, f=1MHz  |         | 4500   |        | pF   |
| Reverce transfer capacitnce             | Crss                | VDS=25V, VGS=0V, f=1MHz  |         | 205    |        | pF   |
| Output capacitance                      | Coss                | VDS=25V, VGS=0V, f=1MHz  |         | 410    |        | pF   |
| Turn-on delay time                      | td(on)              | ID=20A, RL=2.5 $\Omega$ , VDD=50V, Rg=0 $\Omega$ , VGS(+)=10V, VGS(-)=0V |         | 10     |        | ns   |
| Rise time                               | tr                  | ID=20A, RL=2.5 $\Omega$ , VDD=50V, Rg=0 $\Omega$ , VGS(+)=10V, VGS(-)=0V |         | 24     |        | ns   |
| Turn-off delay time                     | td(off)             | ID=20A, RL=2.5 $\Omega$ , VDD=50V, Rg=0 $\Omega$ , VGS(+)=10V, VGS(-)=0V |         | 67     |        | ns   |
| Fall time                               | tf                  | ID=20A, RL=2.5 $\Omega$ , VDD=50V, Rg=0 $\Omega$ , VGS(+)=10V, VGS(-)=0V |         | 47     |        | ns   |
| Diode reverse recovery time             | trr                 | IF=40A, VGS=0V, di/dt=100A/μs  |         | 59     |        | ns   |
| Diode reverse recovery charge           | Qrr                 | IF=40A, VGS=0V, di/dt=100A/μs  |         | 133    |        | nC   |

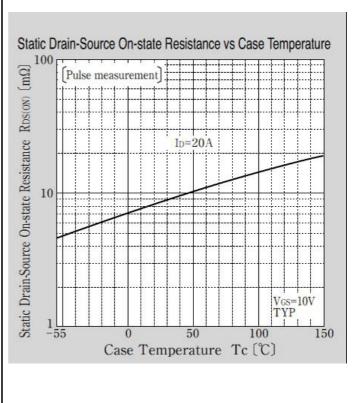
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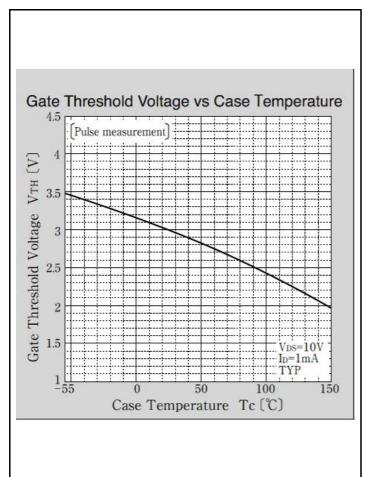
## **CHARACTERISTIC DIAGRAMS**

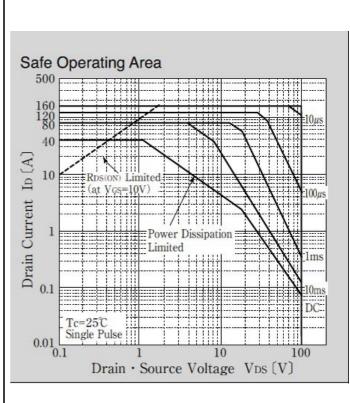


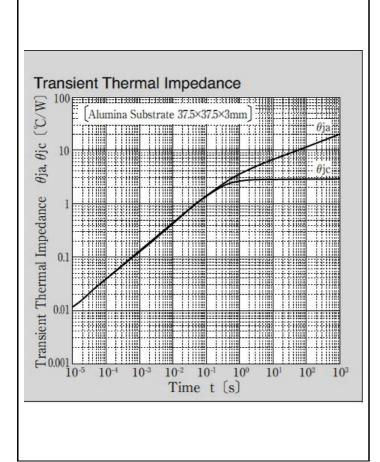


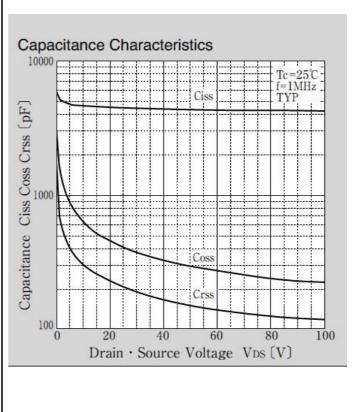


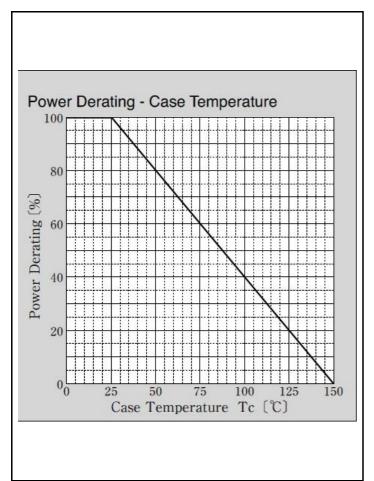


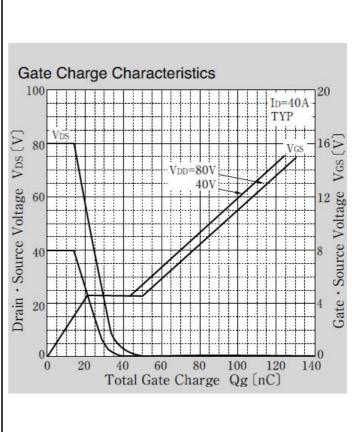


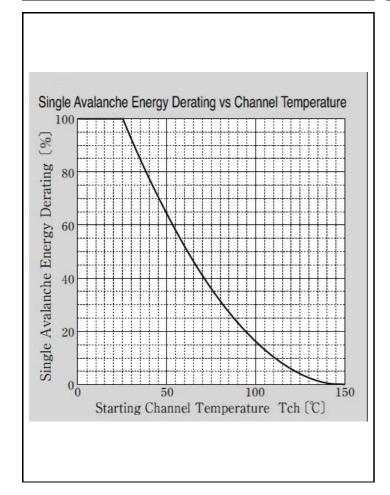










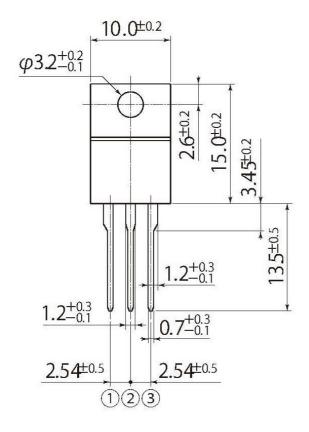


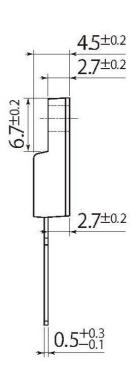
unit:mm

scale: 2/1

**J8** 

| JEDEC Code | _               |  |  |
|------------|-----------------|--|--|
| JEITA Code | SC-91           |  |  |
| House Name | FTO-220AG(3pin) |  |  |





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